[redacted]

- Current transfer ratio (CTR: 20~300% at IF =±1mA, VCE = 5V)
- High isolation voltage between input and output (Viso =5000Vrms)
- Collector - emitter breakdown voltage(BVCEO ≥ 80V
- Operating Temperature: -55 ~110
- Environmentally friendly products, compliant with CQC, UL, and VDE requirements

[redacted]

- Case: DIP4 DIP4-M SMD4
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals:

Xdc

Input	Forward Current	IF	±60	mA
	Power Dissipation	PD	100	mW
	Power Dissipation Derating factor (above Ta = 100℃)	PDD	2.9	mW/℃
	Thermal Resistance Junction-Ambient	RthJ-A	325	℃/W
	Thermal Resistance Junction-Case	RthJ-C	200	℃/W
Output	Power Dissipation	PC	150	mW
	Collector Current	IC	50	mA
	Collector-Emitter Voltage	VCEO	80	V
	Emitter-Collector Voltage	VECO	7	V

Total Power Dissipation	PTOT	200	mW
Isolation Voltage *1	VISO	5000	Vrms
Operating Temperature	TOPR	-55 ~ +100	℃
Storage Temperature Range	TSTG	-55 ~ +125	℃
Soldering Temperature *2	TSOL	260	℃

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Input	Forward Voltage	VF	IF=±20mA	-	1.2	1.4	V
	Terminal Capacitance	Ct	V=0,f=1kHz	-	30	250	pF
	Collector-Emitter Dark Current	ICEO	VCE = 20V, IF = 0	-	-	100	nA
Output	Collector-Emitter Breakdown Voltage						

proof